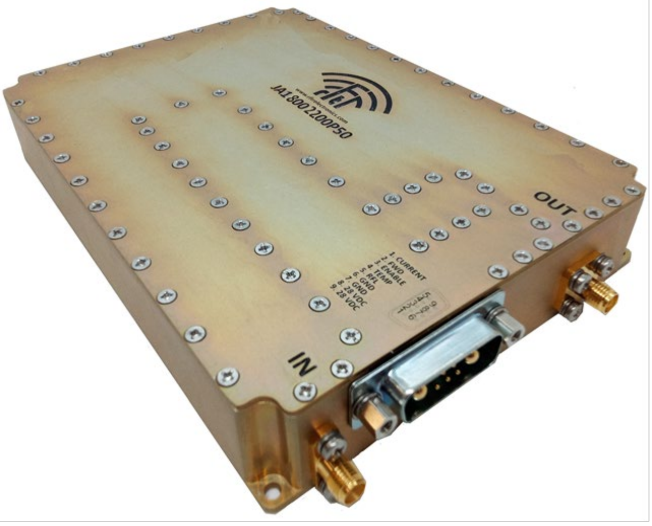
JA18002200P50; 1.8 – 2.2 GHz 100W AMPLIFIER

- **Solid-state Class AB design**
- **GaN on SiC Transistors**
- **High reliability and ruggedness**
- **Forward/Reflected Power Monitorings**
- **Fast Switching Capability**



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

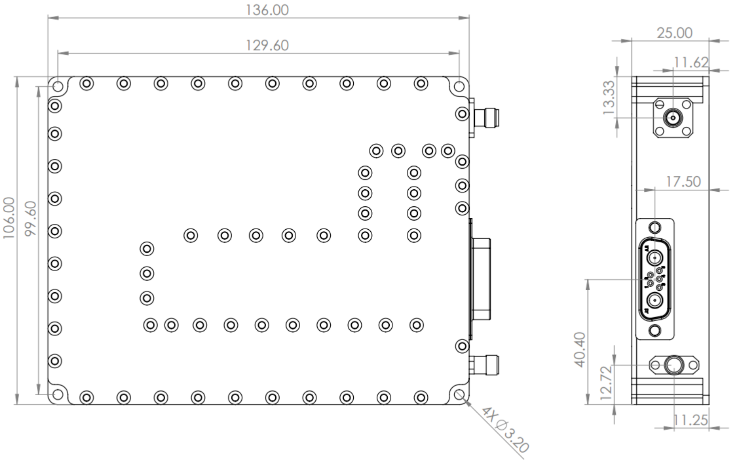
Frequency:	1800 - 2200 MHz
Output Power:	100 W typ.
RF input for Rated Output:	0 dBm typ.
Nominal Gain:	50 dB typ.
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 (Fully Protected)
DC Supply Voltage:	28 V
DC Current:	8.5 A Avg typ.
Enable Speed:	5 µs max.
Operating Case Temp.:	-40 ºC to 85 ºC External Heatsink Required
Storage Temperature:	-40 ºC to 85 ºC

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
7-PIN DSUB:	A1) GND A2) 28V 1) Current 2) Forward Power 3) Enable 4) Temperature 5) Reverse Power

MECHANICAL SPECIFICATIONS

Size (mm) :	136 x 106 x 25
Weight :	570 gr.
Plating :	Yellow Chromate



GENERAL DESCRIPTION

RFTR’s JA18002200P50 is a reliable ultrawide-band 100W power amplifier operating between 1800-2200 MHz and suitable for CW or Pulsed waveforms. This amplifier can be used in different applications such as radars, datalinks, mobile jamming or UAVs. JA18002200P50 offers forward-reverse power monitoring and survives under ∞:1 load VSWR condition. The PA can be enabled/disabled as fast as 5 µs that makes it suitable for power saving during pulsed applications.

JA18002200P50 is designed with the components that do not require any export license.

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